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(54) **CHALCOGENIDE MATERIAL AND
SEMICONDUCTOR DEVICE INCLUDING
THE SAME**

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ABSTRACT

Disclosed is a chalcogenide material including germanium (Ge), selenium (Se), arsenic (As), silicon (Si) and indium (In). In the chalcogenide material, a content of selenium (Se) is 49 at % to 56 at %, a content of indium (In) is 1.1 at % or less, and a sum of contents of germanium (Ge) and silicon (Si) is 18 at % to 21 at %.

